

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch, LCD/LED Back light

Product Summary



V_{DS}	200	V
I_D (at $V_{GS}=10V$)	18	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	170	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	180	m Ω



Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_C=25^{\circ}C$	18	A
Continuous Drain Current, V_{GS} @ 10V ¹	$I_D@T_C=100^{\circ}C$	11.7	A
Pulsed Drain Current ²	I_{DM}	40	A
Single Pulse Avalanche Energy ³	EAS	15	mJ
Avalanche Current	I_{AS}	10	A
Total Power Dissipation ⁴	$P_D@T_C=25^{\circ}C$	83	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	60	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	1.5	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	200	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =9A	---	---	170	mΩ
		V _{GS} =4.5V, I _D =9A	---	---	180	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =160V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =160V, V _{GS} =0V, T _J =55°C	---	---	5	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =9A	---	22	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2	---	Ω
Total Gate Charge	Q _g	V _{DS} =80V, V _{GS} =10V, I _D =9A	---	45	---	nC
Gate-Source Charge	Q _{gs}		---	9	---	
Gate-Drain Charge	Q _{gd}		---	10.5	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω, I _D =9A	---	13	---	ns
Rise Time	T _r		---	8.2	---	
Turn-Off Delay Time	T _{d(off)}		---	25	---	
Fall Time	T _f		---	11	---	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	2047	---	pF
Output Capacitance	C _{oss}		---	109	---	
Reverse Transfer Capacitance	C _{rss}		---	70	---	

Drain-Source Diode Characteristics

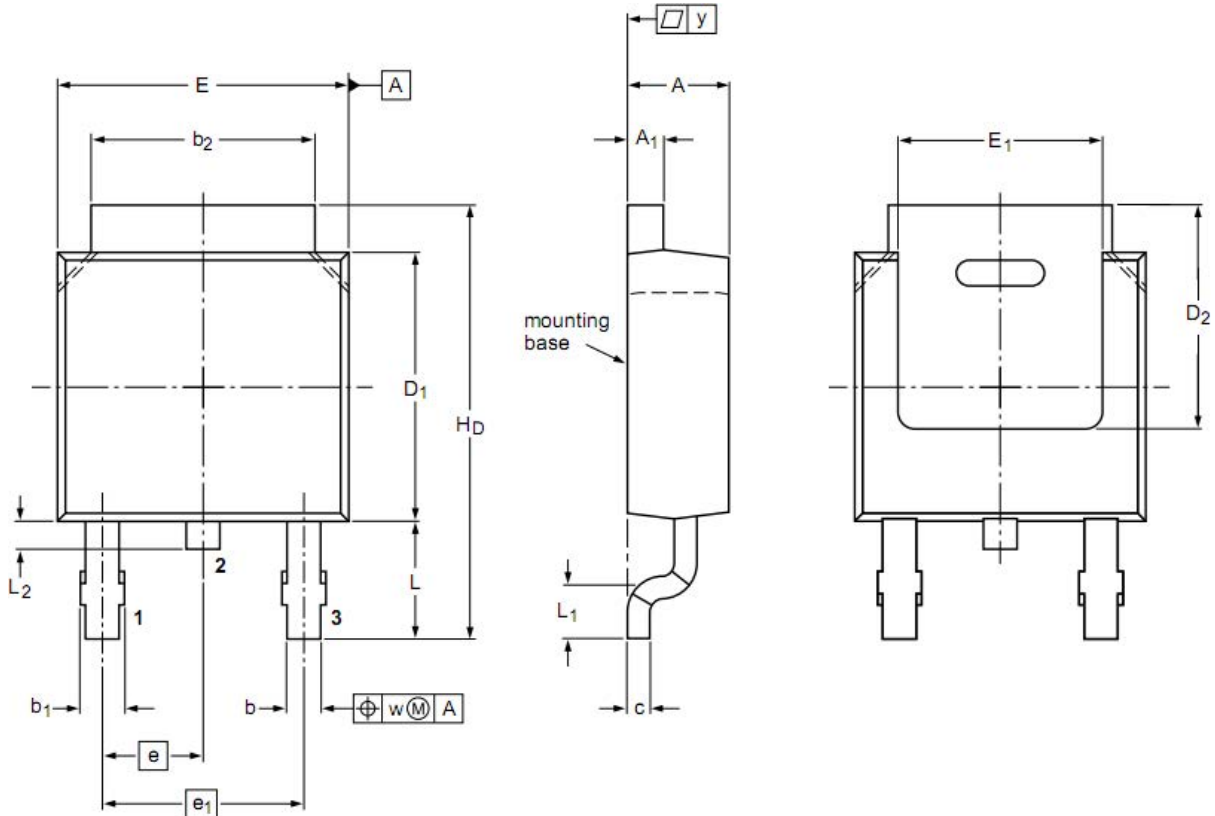
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	18	A
Pulsed Source Current ^{2,5}	I _{SM}		---	---	40	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =10A, di/dt=100A/μs, T _J =25°C	---	37	---	nS
Reverse Recovery Charge	Q _{rr}		---	103	---	nC

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.3mH
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

TO-252 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	2.20	2.30	2.38	E ₁	4.40	--	--
A ₁	0.46	0.50	0.63	e	2.286 BSC		
b	0.64	0.76	0.89	e ₁	--	4.57	--
b ₁	0.77	0.85	1.14	H _D	9.40	10.00	10.40
b ₂	5.00	5.33	5.46	L	2.743 REF		
c	0.458	0.508	0.558	L ₁	1.40	1.52	1.77
D ₁	5.98	6.10	6.223	L ₂	0.50	0.80	1.01
D ₂	5.21	--	--	W	--	0.20	--
E	6.40	6.60	6.731	y	--	--	0.20